

3-phase bridge rectifier + brake chopper +3-phase bridge inverter SK 15 DGDL 065 ET

Preliminary Data

Features

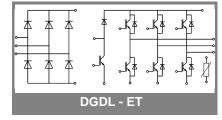
- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL Technology FWD
- Integrated NTC temperature sensor

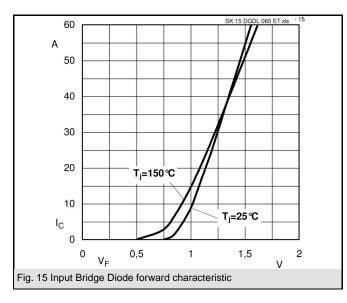
Typical Applications*

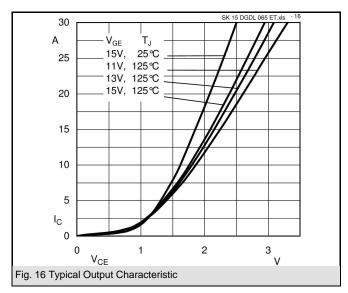
Inverter

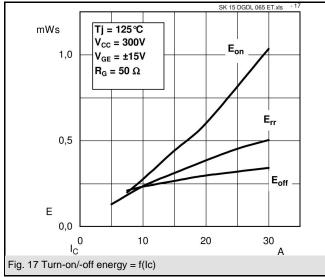
Absolute Maximum Ratings		T _s = 25°C, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		600	V				
I _C	T _s = 25 (80) °C	19 (14)	Α				
I _{CRM}	I_{CRM} = 2 x I_{Cnom} , t_p = 1 ms	30	Α				
V_{GES}		±20	V				
T_{j}		-40 + 150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (80) °C	22 (15)	Α				
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	28	Α				
T_{j}		-40 + 150	°C				
Rectifier							
V_{RRM}		800	V				
I _F	T _s = 80 °C	21	Α				
I_{FSM} / I_{TSM}	$t_{p} = 10 \text{ ms}$, sin 180 °, $T_{i} = 25 \text{ °C}$	220	Α				
I ² t	$t_{\rm p} = 10 \text{ ms}$, sin 180 °, $T_{\rm i} = 25 \text{ °C}$	240	A²s				
T_{j}		-40 + 150	°C				
T _{sol}	Terminals, 10s	260	°C				
T _{stg}		-40 + 125	°C				
V _{isol}	AC, 1 min. / 1s	2500 / 3000	V				
		T 0500 1 11 1	.6. 1				

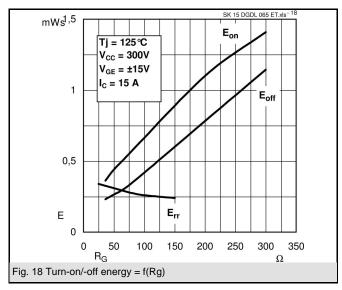
Characteristics		T _s = 25°C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V_{CEsat}	$I_C = 10 \text{ A}, T_j = 25 (125) °C$		2 (2,2)	2,5	V			
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.5 \text{ mA}$	3	4	5	V			
V _{CE(TO)}	T _j = 25 °C (125) °C		1,2 (1,1)	1,2	V			
r _T	$T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$		80 (110)	120	mΩ			
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,8		nF _			
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,2		nF			
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,2		nF			
R _{th(j-s)}	per IGBT			1,9	K/W			
$t_{d(on)}$	under following conditions		45		ns			
t _r	$V_{CC} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$		40		ns			
$t_{d(off)}$	I _C = 10 A, T _j = 125 °C		340		ns			
t _f	$R_{Gon} = R_{Goff} = 125 \Omega$		90		ns			
E _{on}	inductive load		0,3		mJ			
E_{off}			0,22		mJ			
	verter, Chopper							
$V_F = V_{EC}$	I _F = 10 A, T _j = 25(125) °C		1,4 (1,4)	1,7	V			
$V_{(TO)}$	T _j = 25 °C (125) °C		1 (0,9)	1,1	V			
r _T	$T_{j} = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$		45 (50)	60	mΩ			
$R_{th(j-s)}$	per diode			2,3	K/W			
I _{RRM}	under following conditions		11		Α			
Q_{rr}	I _F = 10 A, V _R = 300 V		1,1		μC			
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		0,24		mJ			
	di _{F/dt} = 290 A/µs							
Diode red	tifier	•			•			
V_{F}	I _F = 15 A, T _i = 25() °C	1	1,1		V			
V _(TO)	T _i = 150 °C		0,8		V			
r _T	T _i = 150 °C		20		mΩ			
$R_{th(j-s)}$	per diode			2,7	K/W			
	Temperatur sensor							
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω			
Mechanical data								
w			30		g			
M_s	Mounting torque			2,5	Nm			

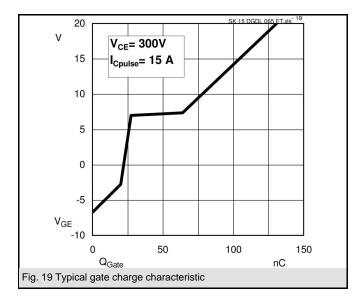


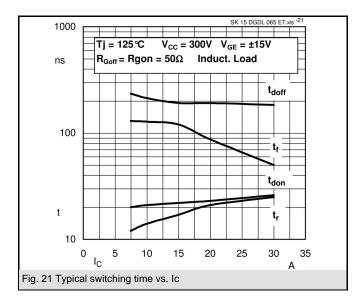


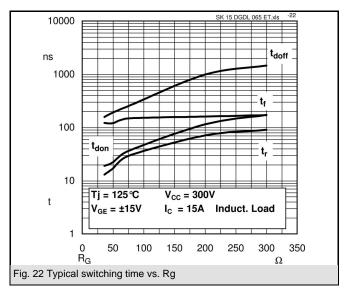


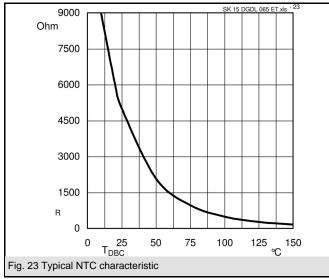


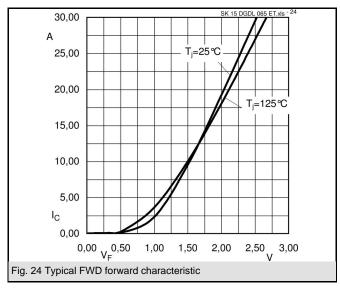


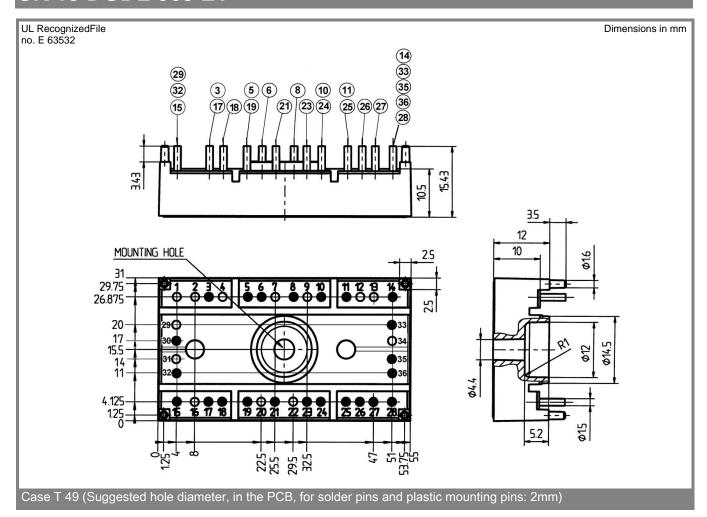


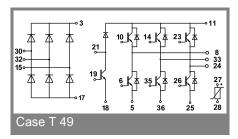












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.